

IRFB260NPbF

HEXFET® Power MOSFET

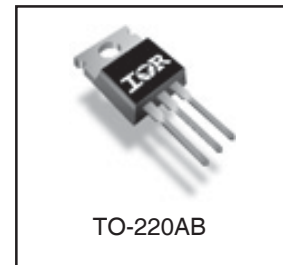
Applications

- High frequency DC-DC converters
- Lead-Free

V_{DSS}	R_{DS(on) max}	I_D
200V	0.040Ω	56A

Benefits

- Low Gate-to-Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective C_{OSS} to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current



Absolute Maximum Ratings

	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	56	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	40	
I _{DM}	Pulsed Drain Current ①	220	
P _D @ T _C = 25°C	Power Dissipation	380	W
	Linear Derating Factor	2.5	W/°C
V _{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery dv/dt ②	10	V/ns
T _J	Operating Junction and	-55 to + 175	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	0.40	°C/W
R _{θCS}	Case-to-Sink, Flat, Greased Surface	0.50	—	
R _{θJA}	Junction-to-Ambient	—	62	

Notes ① through ③ are on page 8

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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	200	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.26	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.040	Ω	$V_{GS} = 10V, I_D = 34A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 200V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 160V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$

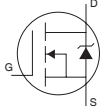
Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	29	—	—	S	$V_{DS} = 50V, I_D = 34A$
Q_g	Total Gate Charge	—	150	220	nC	$I_D = 34A$
Q_{gs}	Gate-to-Source Charge	—	24	37		$V_{DS} = 160V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	67	100		$V_{GS} = 10V$ ④
$t_{d(on)}$	Turn-On Delay Time	—	17	—		$V_{DD} = 100V$
t_r	Rise Time	—	64	—	ns	$I_D = 34A$
$t_{d(off)}$	Turn-Off Delay Time	—	52	—		$R_G = 1.8\Omega$
t_f	Fall Time	—	50	—		$V_{GS} = 10V$ ④
C_{iss}	Input Capacitance	—	4220	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	580	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	140	—		$f = 1.0\text{MHz}$
C_{oss}	Output Capacitance	—	5080	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$
C_{oss}	Output Capacitance	—	230	—		$V_{GS} = 0V, V_{DS} = 160V, f = 1.0\text{MHz}$
$C_{oss\ eff.}$	Effective Output Capacitance	—	500	—		$V_{GS} = 0V, V_{DS} = 0V\ \text{to}\ 160V$ ⑤

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	450	mJ
I_{AR}	Avalanche Current①	—	34	A
E_{AR}	Repetitive Avalanche Energy①	—	38	mJ

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	56	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	220		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 34A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	240	360	ns	$T_J = 25^\circ\text{C}, I_F = 34A$
Q_{rr}	Reverse Recovery Charge	—	2.1	3.2	μC	$di/dt = 100A/\mu s$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

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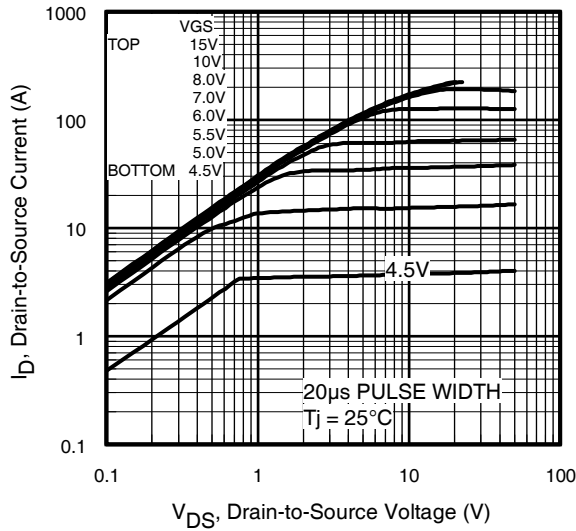


Fig 1. Typical Output Characteristics

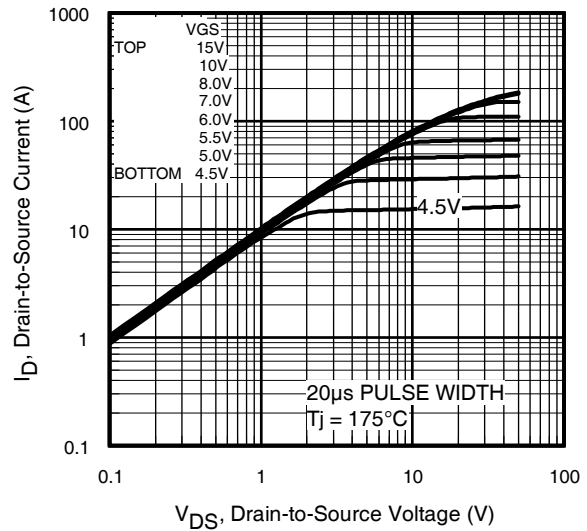


Fig 2. Typical Output Characteristics

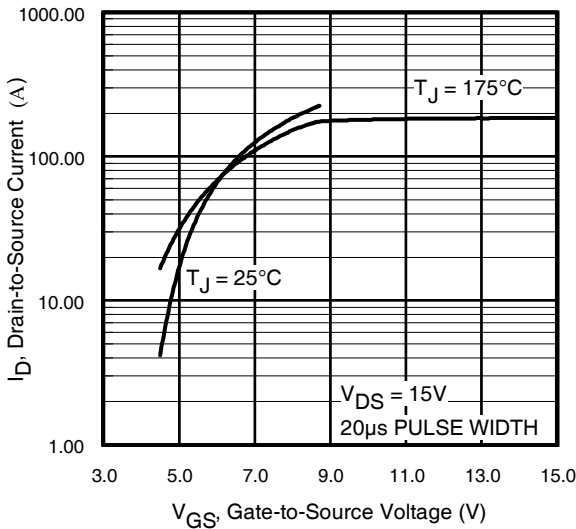


Fig 3. Typical Transfer Characteristics

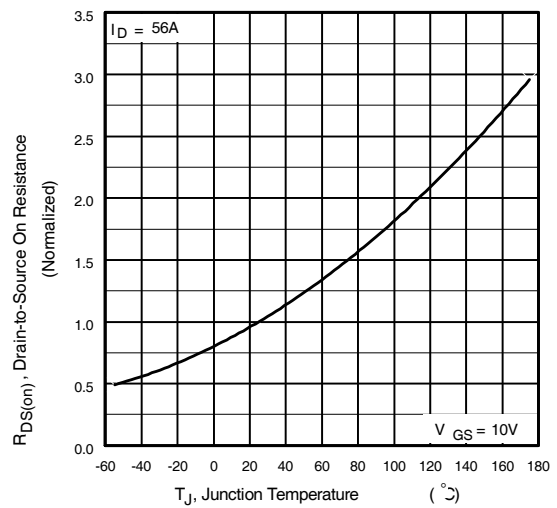


Fig 4. Normalized On-Resistance Vs. Temperature

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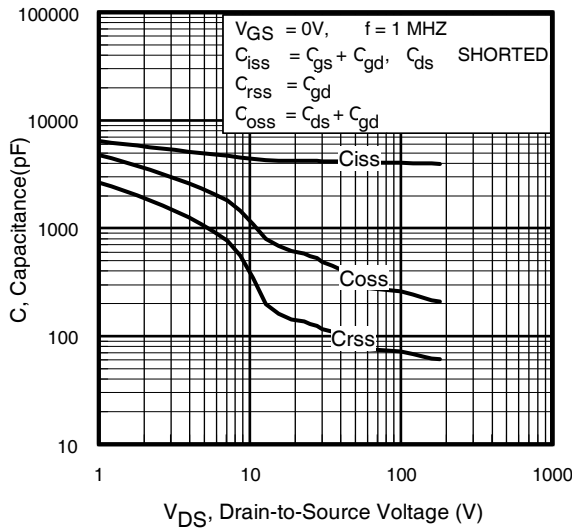


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

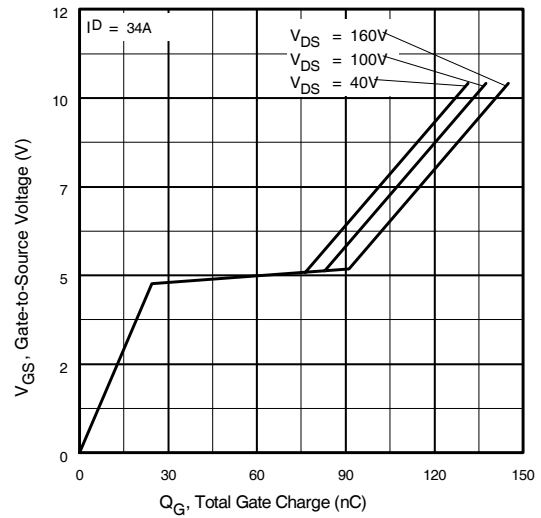


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

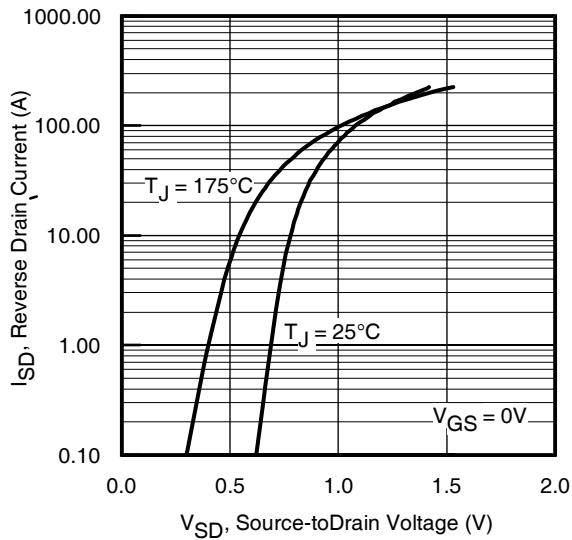


Fig 7. Typical Source-Drain Diode Forward Voltage

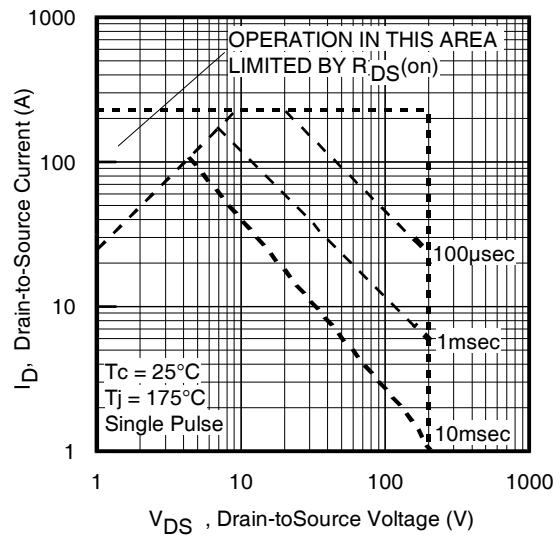


Fig 8. Maximum Safe Operating Area

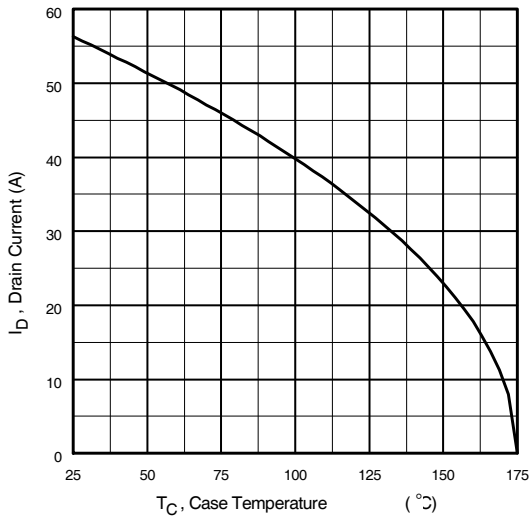


Fig 9. Maximum Drain Current Vs. Case Temperature



Fig 10a. Switching Time Test Circuit



Fig 10b. Switching Time Waveforms

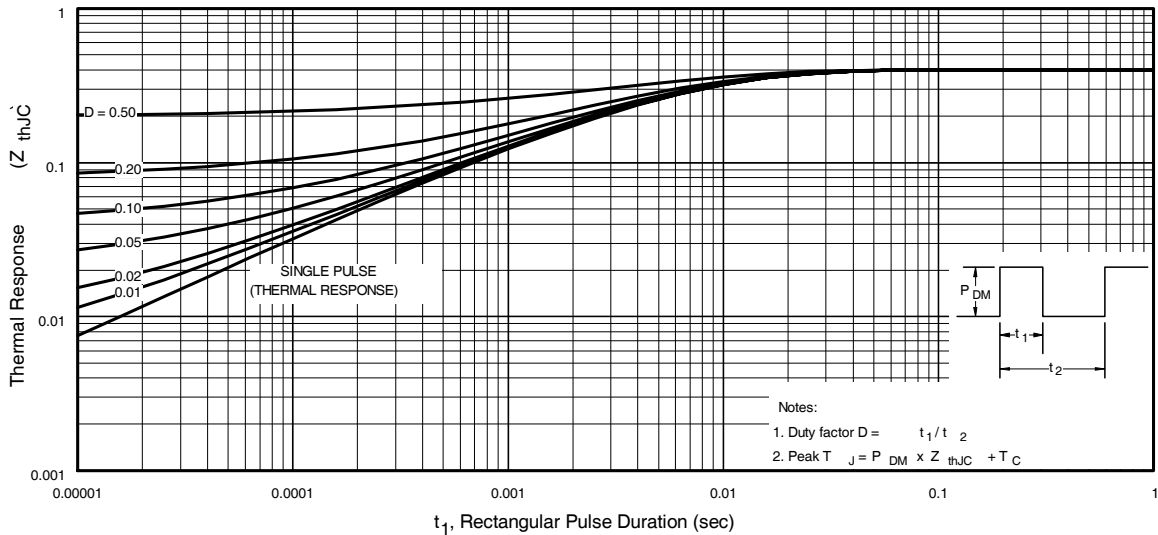


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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Fig 12a. Unclamped Inductive Test Circuit



Fig 12b. Unclamped Inductive Waveforms

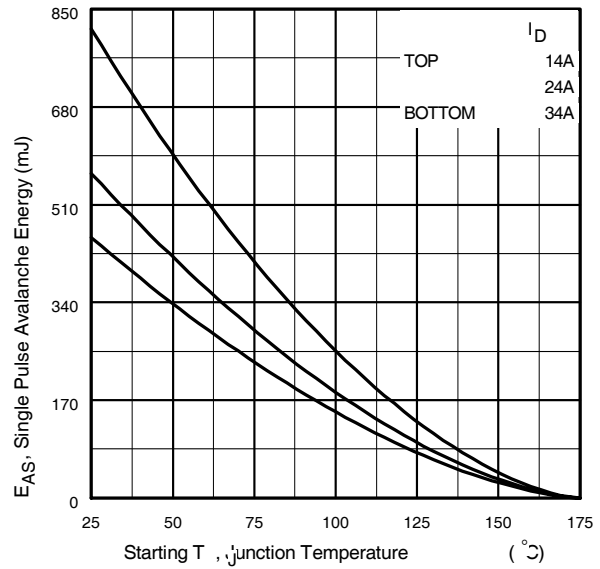


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

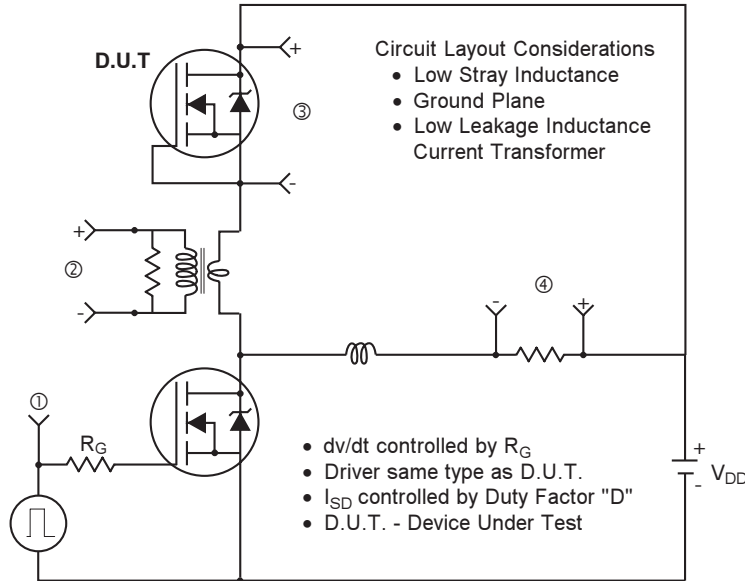


Fig 13a. Basic Gate Charge Waveform



Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



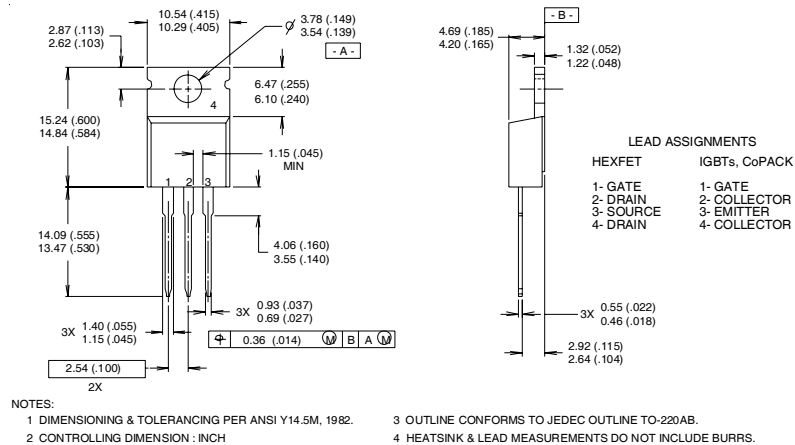
* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-Channel HEXFET® Power MOSFETs

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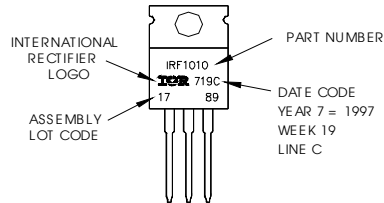
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TO-220AB Package Outline



TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"
Note: "P" in assembly line
 position indicates "Lead-Free"



Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.78\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 34\text{A}$.
- ③ $I_{SD} \leq 34$, $di/dt \leq 480\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$,
 $T_J \leq 175^\circ\text{C}$
- ④ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.
- ⑤ C_{OSS} eff. is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 80% V_{DS}

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Industrial market.
 Qualification Standards can be found on IR's Web site.

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IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
 TAC Fax: (310) 252-7903

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